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→ J. Minnee

14/02/96

Motorola Semiconductors S.A.
Discrete & Analog Products Division

ETC -

ESA-QCA0075T-C

TOTAL DOSE EFFECTS CHARACTERIZATION

RESULTS FOR LM111H

ORIGINAL
EN ROUGE

Ref : MOT/RAD.0043

DATE CODE : 9504

DIFFUSION LOT : 1A338506
WAFER N° : M80T1

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		TOTAL DOSE TEST PLAN No. N° MOT/RAD.0043					ISSUE No : 0 DATE : 07/03/95 PAGE : 1/2					
SCC COMPONENT No 9103 002 07B		COMPONENT DESIGNATION LM111H					IRRADIATION SPEC : ISSUE :					
SPECIFICATIONS GENERIC : 9000 ISSUE REV. DETAIL 9103 002 ISSUE REV.		ACCEPTANCE DIFFUSION <input type="checkbox"/> LOT <input type="checkbox"/>		SAMPLE SIZE 10 (Sn° 1 to 10) CONTROL DEVICES 1 (Sn° 11)			PROJECT					
FAMILY LINEAR		GROUP IC'S					PACKAGE TO99					
MANUFACTURER NAME MOTOROLA ADDRESS : AVENUE GENERAL EISENHOWER 31023 TOULOUSE CEDEX - FRANCE		TEST HOUSE NAME MOTOROLA ADDRESS : AVENUE GENERAL EISENHOWER 31023 TOULOUSE CEDEX - FRANCE					ORIGINATOR NAME ALCATEL BELL TELEPHONE :					
FACILITY SOURCE C060 DERTS AVENUE E. BELIN 31055 TOULOUSE CEDEX - FRANCE		IRRADIATION SINGLE <input type="checkbox"/> MULTIPLE <input checked="" type="checkbox"/>		IRRADIATION MEASUREMENT INTERVAL BIASED <input type="checkbox"/> UNBIASED <input checked="" type="checkbox"/> TEMP °C			CIRCUIT REF SUPPLY VOLTAGE		LEVEL OF INTEREST			
SINGLE IRRADIATION		MULTIPLE IRRADIATION STEPS			1	2	3	4	5	6	7	8
DOSE (KRAD) (Si)		DOSE KRADS (Si)			10	20	30	50				
DOSE RATE (RAD) (Si)		DOSE RATE (KRADS) (Si)			5,7	5,7	5,7	5,7				
EXPOSURE TIME		EXPOSURE TIME (mn)			105'	105'	105'	210'				
IRRADIATION CONDITIONS BIASED (REMOTE TEST) <input checked="" type="checkbox"/> BIAS CIRCUIT REF (SEE P 5) UNBIASED (REMOTE TEST) <input type="checkbox"/> SUPPLY VOLTAGE ±15V IN-SITU TEST <input type="checkbox"/> TEMP °C : 25					ANNEAL TEST ? YES BIASED <input checked="" type="checkbox"/> BIAS CIRCUIT REF (SEE P 5) UNBIASED <input type="checkbox"/> SUPPLY VOLTAGES ±15 V TEMP °C : 25° DURATION : 168 h							
ELECTRICAL PARAMETERS TO BE TESTED : TABLE 2A OF ESA / SCC DETAIL SPECIFICATION N° 9103 002												

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TOTAL DOSE TEST PLAN No.
N° MOT/RAD.0043

ISSUE No : 0 REV :
DATE : 07/03/95 DATE :
PAGE : 2/2

IRRADIATION TEST SEQUENCE (SEE PAGE 6)

TEST STEP	DESCRIPTION	REQUIREMENTS

REMARKS

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1 - TOTAL DOSE EFFECTS CHARACTERIZATION SUMMARY

NUMBER OF IRRADIATED DEVICES	10
IRRADIATION STEPS (KRADS [Si])	10 - 20 - 30 - 50
1ST PARAMETERS OUT OF SPECIFICATION	After an irradiation of 10Krad, small drifts on IIO parameter are found on several parts. The worst case value is at this level 14,4nA. (specified limit : $\pm 10nA$).
2ND PARAMETER OUT OF SPECIFICATION	After an irradiation of 50Krad one part shows a weak drift on VIO parameter since the worst case value found is -2,093mV (specified limit: $\pm 2mv$).
LOST OF FUNCTIONALITY	All the tested devices stay functional during this radiation evaluation.

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2 - DEVICES IDENTIFICATION

DEVICE IDENTIFICATION NUMBER : LM111H

MANUFACTURER : MOTOROLA

DATE CODE : 9504

SERIAL NUMBERS : 1 - 2 - 3 - 4 - 5 - 6 - 7 - 8 - 9 - 10

CORRELATION PART : N° 11

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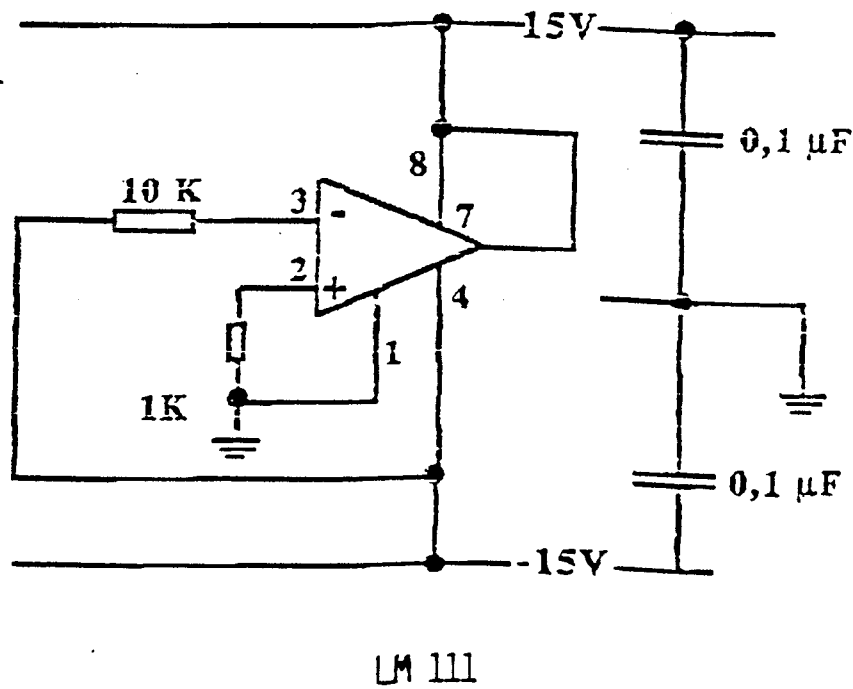


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3 - IRRADIATION CONDITIONS

3.1) POLARIZATION CONDITIONS





3.2) IRRADIATION PLAN

DATE	TIME	TOTAL DOSE (KRADS)	DOSE RATE (KRADS / H)
21.02.95	105'	10	5,7
21.02.95	105'	20	5,7
21.02.95	105'	30	5,7
21.02.95	210'	50	5,7

NOTE

Between two irradiation steps a read and record measurement was performed at MOTOROLA plant.

The time interval between exposure and re-exposure was 2H. The measurements were performed in a time interval of 1H after the exposure.

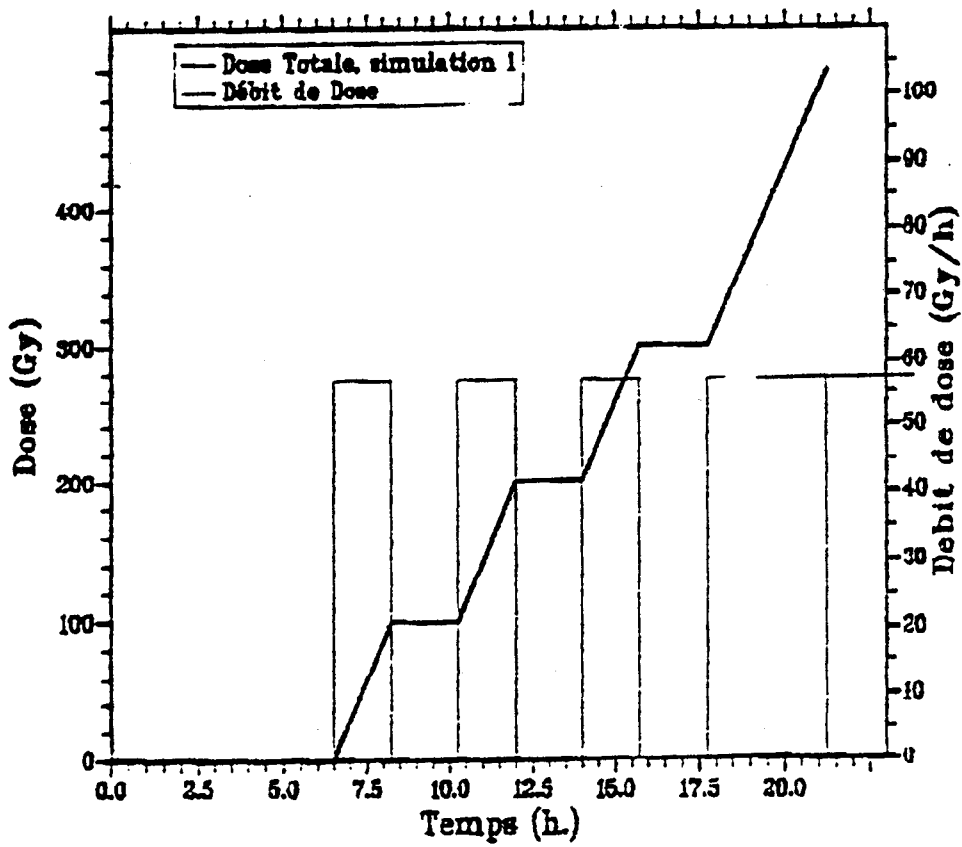
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3.3) IRRADIATION PROFILE



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3.4) IRRADIATION EQUIPMENT

Irradiations were performed with the CERT-DERT CO60 source (Gammacell 220) in TOULOUSE (31). The dose rate was 5,7 Krads / h. The exposure was done at ambient temperature

4 - MEASUREMENT CONDITIONS

Measurements were done according ESA / SCC 9103/002 detail specification table 2 on a LTX equipment.

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5 - RESULTS

5.1) DATALOGS

ESA / SCC table 2A datalogs including measurement conditions are shown in appendix 1. Part number 11 is the correlation component.

5.2) DIAGRAMS

Diagrams corresponding to ESA / SCC 9103 / 002 detail specification table 4 are shown in appendix 2. Specification limits and statistical information are given.

5.3) TOTAL DOSE HARDNESS

The following table sums up the radiation hardness results of the 10 irradiated parts.

TOTAL DOSE (KRADS)	0	10	20	30	50	annealing
NUMBER OF IN SPECIFICATION DEVICE	10/10	2/10	1/10	1/10	0/10	1/10
NUMBER OF IN SPECIFICATION PARAMETERS FOR ALL DEVICES	21/21	19/21	18/21	18/21	17/21	17/21

NOTE

The 21 parameters of ESA/SCC table2A detail specification have been measured.

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5.4) COMMENTS

IIO parameter:

After an irradiation of 10Krads, most of parts show weak drifts on IIO parameter. The values found are around the specified limit ($\pm 10\text{nA}$). However, two parts present a worst case value of 14,4nA. At the total dose level of 20Krads, the IIO worst case value reach 21nA. This value is a saturation one since IIO parameter keep it all along the remaining evaluation phases. No rebound is found during the room temperature annealing.

VIO parameter:

After an irradiation of 50Krads, one part shows a very small drift on VIO parameter. The worst case value found is -2,093mV for a specified limit at $\pm 2\text{mV}$. No evolution of this drift is found during the annealing phase.

5.5) SYNTHESIS SUMMARY :

All the tested parts have been found functional during this radiation verification test. IIO parameters were found out of the ESA/SCC table 2 specification but the corresponding drifts are rather limited and reach a saturation value around 21nA. We think that this drift come from the differents IC input transistor states under irradiation due to the polarization condition applied on the LM111H devices.



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APPENDIX 1

TABLE 2 (A) RESULTS AFTER

0 Krad, 10 Krads,

20 Krads, 30 Krads and 50 Krads

AND AFTER 168 h of annealing

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ELECTRICAL MEASUREMENTS

BEFORE RADIATION

DC AT 25 °C



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TRACEABILITY INFORMATION

PROCESS LOT NUMBER	NTTA0111H
DEVICE	TY38356H
SOURCE TYPE	LM111H
DATE CODE	9504
CUSTOMER	VARIOUS
CUSTOMER PART NUMBER	SCC 9103 002 07B
LOT SIZE	11
SERIAL NUMBER RANGE	1-11
MEASUREMENT TYPE	25 C RADIATION TESTING
DATE	03-MAR-95

COMMENTS

**TABLE 2A DC PARAMETERS
ELECTRICAL RECORDS BEFORE RADIATION TESTING**

PARAMETERS TEST CONDITIONS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
VCC	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	29.500 V	29.500 V	29.500 V	2.500 V
VEE	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-500.000 mV	-500.000 mV	-500.000 mV	-2.500 V
VIC	0.000 V						-14.500 V	-14.500 V	-14.500 V	0.000 V
V6					15.000 V	15.000 V				
V5						15.000 V				

LIMITS

MIN	-2.000 mV	-10.000 nA	0.000 A	0.000 A	-2.000 mV	-10.000 nA	-10.000 nA	0.000 A	0.000 A	-2.000 mV
MAX	2.000 mV	10.000 nA	100.000 nA	100.000 nA	2.000 mV	10.000 nA	10.000 nA	100.000 nA	100.000 nA	2.000 mV

DATA RECORDS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
Unit	mV	nA	nA	nA	mV	nA	pA	nA	nA	mV
1	-1.373	0.002	48.902	48.900	-1.193	3.596	1.000	59.938	59.937	-1.731
2	-1.014	0.112	37.715	37.604	-1.014	3.596	18.000	63.562	63.543	-1.553
3	-0.467	0.004	27.005	27.001	-0.469	0.549	3.000	45.555	45.552	-1.014
4	-1.194	0.003	52.736	52.733	-0.834	3.601	12.000	67.146	67.135	-1.552
5	-0.649	0.005	38.249	38.244	-0.649	3.738	3.000	45.563	45.560	-1.015
6	-0.287	0.166	34.626	34.460	-0.287	3.611	9.000	41.814	41.805	-0.833
7	-1.014	0.007	38.267	38.260	-0.834	0.082	9.000	56.323	56.313	-1.373
8	-1.013	0.003	49.127	49.124	-0.648	3.714	2.000	63.541	63.539	-1.373
9	-0.835	0.014	38.253	38.238	-0.649	0.006	7.000	56.362	56.355	-1.374
10	-0.648	3.757	34.414	30.657	-0.289	0.526	12.000	52.755	52.742	-1.014
11	-0.469	0.000	30.875	30.875	-0.290	0.008	4.000	38.273	38.268	-0.836
MEAN	-814.818uV	370.273pA	39.106nA	38.736nA	-650.545uV	2.093nA	7.273pA	53.712nA	53.704nA	-1.243mV
SIGMA	338.948uV	1.125nA	8.016nA	8.320nA	303.234uV	1.789nA	5.293pA	9.698nA	9.696nA	311.657uV
MIN	-1.373mV	-0.000 A	27.005nA	27.001nA	-1.193mV	6.000pA	1.000pA	38.273nA	38.268nA	-1.731mV
MAX	-287.000uV	3.757nA	52.736nA	52.733nA	-287.000uV	3.738nA	18.000pA	67.146nA	67.135nA	-833.000uV
QTY	11	11	11	11	11	11	11	11	11	11

TOTAL PASSED DEVICES : 11

TOTAL FAILED DEVICES : 0

NO REJECTED UNITS.

PARAMETERS TEST CONDITIONS

Test Nb	38.0
Test	II
VCC	18.000 V
VEE	-18.000 V

LIMITS

MIN	0.000 A
MAX	20.000 nA

DATA RECORDS

Test Nb	38.0
Test	II
Unit	pA

1	4.000
2	7.000
3	5.000
4	5.000
5	4.000
6	3.000
7	2.000
8	8.000
9	3.000
10	3.000

11	3.000
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MEAN	4.273pA
SIGMA	1.849pA
MIN	2.000pA
MAX	8.000pA
QTY	11

TOTAL PASSED DEVICES : 11

TOTAL FAILED DEVICES : 0

NO REJECTED UNITS.

ELECTRICAL MEASUREMENTS

AFTER 10 KRad

DC AT 25 °C



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TRACEABILITY INFORMATION

PROCESS LOT NUMBER	NTTA0111H
DEVICE	TY38356H
SOURCE TYPE	LM111H
DATE CODE	9504
CUSTOMER	VARIOUS
CUSTOMER PART NUMBER	SCC 9103 002 07B
LOT SIZE	11
SERIAL NUMBER RANGE	1-11
MEASUREMENT TYPE	25 C RADIATION TESTING
DATE	03-MAR-95
COMMENTS	

TABLE 2A DC PARAMETERS
ELECTRICAL RECORDS AFTER 10 Krad

PARAMETERS TEST CONDITIONS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
VCC	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	29.500 V	29.500 V	29.500 V	2.500 V
VEE	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-500.000 mV	-500.000 mV	-500.000 mV	-2.500 V
VIC	0.000 V						-14.500 V	-14.500 V	-14.500 V	0.000 V
V6					15.000 V	15.000 V				
V5						15.000 V				

LIMITS

MIN	-2.000 mV	-10.000 nA	0.000 A	0.000 A	-2.000 mV	-10.000 nA	-10.000 nA	0.000 A	0.000 A	-2.000 mV
MAX	2.000 mV	10.000 nA	100.000 nA	100.000 nA	2.000 mV	10.000 nA	10.000 nA	100.000 nA	100.000 nA	2.000 mV

DATA RECORDS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
Unit	mV	nA	nA	nA	mV	nA	nA	nA	nA	mV
1 F	-1.378	3.603	56.410	52.807	-1.199	10.931 *	3.593	67.228	63.635	-1.736
2 F	-1.199	3.598	52.678	49.080	-1.019	10.888 *	7.326	67.243	59.917	-1.557
3	-0.651	3.596	45.615	42.020	-0.471	7.194	7.189	52.807	45.617	-1.017
4 F	-1.200	0.026	56.633	56.607	-0.840	10.928 *	7.191	67.251	60.059	-1.557
5 F	-0.650	3.585	41.828	38.244	-0.650	10.800 *	7.176	56.363	49.186	-1.195
6	-0.471	7.200	41.885	34.685	-0.291	3.580	3.593	52.791	49.198	-1.016
7 F	-1.015	3.595	49.081	45.486	-0.836	14.486 *	3.736	63.574	59.838	-1.554
8 F	-1.018	3.582	49.197	45.615	-0.937	14.424 *	7.325	67.219	59.894	-1.555
9 F	-0.838	0.006	49.108	49.102	-0.652	10.790 *	7.307	63.611	56.304	-1.377
10 F	-0.650	7.381	37.939	30.558	-0.291	3.584	10.778 *	60.015	49.238	-1.016
11	-0.291	3.609	23.936	20.328	-0.290	3.128	0.005	45.591	45.586	-0.836
MEAN	-851.000uV	3.616nA	45.846nA	42.230nA	-670.545uV	9.158nA	5.929nA	60.336nA	54.407nA	-1.311mV
SIGMA	339.763uV	2.301nA	9.388nA	10.600nA	309.514uV	4.161nA	2.913nA	7.473nA	6.685nA	304.000uV
MIN	-1.378mV	6.000pA	23.936nA	20.328nA	-1.199mV	3.128nA	5.000pA	45.591nA	45.586nA	-1.736mV
MAX	-291.000uV	7.381nA	56.633nA	56.607nA	-290.000uV	14.486nA	10.778nA	67.251nA	63.635nA	-836.000uV
QTY	11	11	11	11	11	11	11	11	11	11

TOTAL PASSED DEVICES : 3
 TOTAL FAILED DEVICES : 8
 REJECTED UNITS:

1,2,4,5,7,8,9,10

PARAMETERS TEST CONDITIONS

Test Nb	38.0
Test	II
VCC	18.000 V
VEE	-18.000 V

LIMITS

MIN	0.000 A
MAX	20.000 nA

DATA RECORDS

Test Nb	38.0
Test	II
Unit	pA

1	4.000
2	5.000
3	5.000
4	6.000
5	7.000
6	8.000
7	5.000
8	4.000
9	4.000
10	6.000

11	3.000
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MEAN	5.182pA
SIGMA	1.471pA
MIN	3.000pA
MAX	8.000pA
QTY	11

TOTAL PASSED DEVICES : 11
TOTAL FAILED DEVICES : 0
NO REJECTED UNITS.

ELECTRICAL MEASUREMENTS

AFTER 20 KRad

DC AT 25 °C



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HIGH RELIABILITY DIVISION

TRACEABILITY INFORMATION

PROCESS LOT NUMBER	NTTA0111H
DEVICE	TY38356H
SOURCE TYPE	LM111H
DATE CODE	9504
CUSTOMER	VARIOUS
CUSTOMER PART NUMBER	SCC 9103 002 07B
LOT SIZE	11
SERIAL NUMBER RANGE	1-11
MEASUREMENT TYPE	25 C RADIATION TESTING
DATE	03-MAR-95

COMMENTS

**TABLE 2A DC PARAMETERS
ELECTRICAL RECORDS AFTER 20 Krad**

PARAMETERS TEST CONDITIONS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
VCC	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	29.500 V	29.500 V	29.500 V	2.500 V
VEE	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-500.000 mV	-500.000 mV	-500.000 mV	-2.500 V
VIC	0.000 V						-14.500 V	-14.500 V	-14.500 V	0.000 V
V6					15.000 V	15.000 V				
V5						15.000 V				

LIMITS

MIN	-2.000 mV	-10.000 nA	0.000 A	0.000 A	-2.000 mV	-10.000 nA	-10.000 nA	0.000 A	0.000 A	-2.000 mV
MAX	2.000 mV	10.000 nA	100.000 nA	100.000 nA	2.000 mV	10.000 nA	10.000 nA	100.000 nA	100.000 nA	2.000 mV

DATA RECORDS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
Unit	mV	nA	nA	nA	mV	nA	nA	nA	nA	mV
1 F	-1.378	7.195	56.418	49.223	-1.199	21.697 *	7.185	63.625	56.440	-1.916
2 F	-1.199	7.204	56.419	49.215	-1.018	18.090 *	10.910 *	63.625	52.715	-1.556
3 F	-0.653	10.751 *	41.941	31.190	-0.472	7.171	7.169	60.050	52.881	-1.198
4 F	-1.378	11.166 *	56.273	45.107	-0.839	14.507 *	7.199	70.781	63.582	-1.736
5 F	-0.837	11.050 *	41.793	30.743	-0.651	10.781 *	10.775 *	52.820	42.045	-1.196
6	-0.472	7.195	41.795	34.601	-0.291	3.578	3.602	49.195	45.593	-1.017
7 F	-1.018	7.331	56.424	49.094	-0.840	14.513 *	10.906 *	67.241	56.335	-1.557
8 F	-1.197	7.185	56.402	49.218	-0.652	10.775 *	14.541 *	67.216	52.675	-1.555
9 F	-1.017	7.322	45.565	38.243	-0.650	10.778 *	14.517 *	52.804	38.287	-1.554
10 F	-0.652	7.202	37.881	30.680	-0.292	3.583	10.783 *	56.411	45.628	-1.198
11	-0.290	0.090	31.101	31.012	-0.292	0.002	0.011	34.700	34.689	-0.838
MEAN	-0.917mV	7.608nA	47.456nA	39.848nA	-654.182uV	10.498nA	8.873nA	58.043nA	49.170nA	-1.393mV
SIGMA	366.148uV	3.032nA	9.253nA	8.524nA	304.196uV	6.576nA	4.409nA	10.382nA	8.688nA	725.740uV
MIN	-1.378mV	90.000pA	31.101nA	30.680nA	-1.199mV	2.000pA	11.000pA	34.700nA	34.689nA	-1.916mV
MAX	-290.000uV	11.166nA	56.424nA	49.223nA	-291.000uV	21.697nA	14.541nA	70.781nA	63.582nA	-838.000uV
QTY	11	11	11	11	11	11	11	11	11	11

TOTAL PASSED DEVICES : 2
 TOTAL FAILED DEVICES : 9
 REJECTED UNITS:

1,2,3,4,5,7,8,9,10

PARAMETERS TEST CONDITIONS

Test Nb 38.0
Test II
VCC 18.000 V
VEE -18.000 V

LIMITS

MIN 0.000 A
MAX 20.000 nA

DATA RECORDS

Test Nb 38.0
Test II
Unit pA

1 2.000
2 5.000
3 7.000
4 8.000
5 7.000
6 7.000
7 6.000
8 5.000
9 3.000
10 6.000

11 5.000

MEAN 5.545pA
SIGMA 1.809pA
MIN 2.000pA
MAX 8.000pA
QTY 11

TOTAL PASSED DEVICES : 11
TOTAL FAILED DEVICES : 0
NO REJECTED UNITS.

ELECTRICAL MEASUREMENTS

AFTER 30 KRad

DC AT 25 °C



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MOTOROLA Semiconductors

HIGH RELIABILITY DIVISION

TRACEABILITY INFORMATION

PROCESS LOT NUMBER	NTTA0111H
DEVICE	TY38356H
SOURCE TYPE	LM111H
DATE CODE	9504
CUSTOMER	VARIOUS
CUSTOMER PART NUMBER	SCC 9103 002 07B
LOT SIZE	11
SERIAL NUMBER RANGE	1-11
MEASUREMENT TYPE	25 C RADIATION TESTING
DATE	03-MAR-95

COMMENTS

**TABLE 2A DC PARAMETERS
ELECTRICAL RECORDS AFTER 30 Krad**

PARAMETERS TEST CONDITIONS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
VCC	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	29.500 V	29.500 V	29.500 V	2.500 V
VEE	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-500.000 mV	-500.000 mV	-500.000 mV	-2.500 V
VIC	0.000 V						-14.500 V	-14.500 V	-14.500 V	0.000 V
V6					15.000 V	15.000 V				
V5						15.000 V				

LIMITS

MIN	-2.000 mV	-10.000 nA	0.000 A	0.000 A	-2.000 mV	-10.000 nA	-10.000 nA	0.000 A	0.000 A	-2.000 mV
MAX	2.000 mV	10.000 nA	100.000 nA	100.000 nA	2.000 mV	10.000 nA	10.000 nA	100.000 nA	100.000 nA	2.000 mV

DATA RECORDS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
Unit	mV	nA	nA	nA	mV	A	nA	nA	nA	mV
1 F	-1.378	10.874 *	60.040	49.166	-1.198	21.698n*	18.102 *	60.023	41.921	-1.916
2 F	-1.198	10.919 *	63.631	52.712	-1.017	18.095n*	18.094 *	70.767	52.672	-1.735
3 F	-0.652	10.785 *	45.582	34.797	-0.472	7.196n	7.200	52.809	45.609	-1.197
4 F	-1.377	10.805 *	59.243	48.438	-0.838	14.505n*	14.508 *	74.421	59.913	-1.736
5 F	-0.836	14.684 *	41.872	27.188	-0.650	10.793n*	10.782 *	60.000	49.218	-1.375
6	-0.472	7.186	41.687	34.501	-0.292	3.592n	3.589	56.411	52.822	-1.018
7 F	-1.195	10.901 *	56.038	45.137	-0.836	14.517n*	14.496 *	67.051	52.556	-1.555
8 F	-1.196	10.921 *	59.993	49.072	-0.650	10.782n*	14.537 *	74.505	59.968	-1.734
9 F	-1.017	10.907 *	56.398	45.491	-0.651	10.803n*	14.517 *	63.585	49.069	-1.556
10 F	-0.837	14.762 *	52.803	38.041	-0.291	3.572n	10.790 *	59.899	49.109	-1.197
11	-0.291	3.614	30.754	27.140	-0.291	1.000p	0.005	41.888	41.883	-0.837
MEAN	-0.950mV	10.578nA	51.640nA	41.062nA	-653.273uV	10.505nA	11.511nA	61.942nA	50.431nA	-1.441mV
SIGMA	364.607uV	3.082nA	10.260nA	9.132nA	303.715uV	6.576nA	5.811nA	9.737nA	6.082nA	343.268uV
MIN	-1.378mV	-3.614nA	30.754nA	27.140nA	-1.198mV	1.000pA	5.000pA	41.888nA	41.883nA	-1.916mV
MAX	-291.000uV	14.762nA	63.631nA	52.712nA	-291.000uV	21.698nA	18.102nA	74.505nA	59.968nA	-837.000uV
QTY	11	11	11	11	11	11	11	11	11	11

TOTAL PASSED DEVICES : 2
 TOTAL FAILED DEVICES : 9
 REJECTED UNITS:

1,2,3,4,5,7,8,9,10

PARAMETERS TEST CONDITIONS

Test Nb 38.0
Test II
VCC 18.000 V
VEE -18.000 V

LIMITS

MIN 0.000 A
MAX 20.000 nA

DATA RECORDS

Test Nb 38.0
Test II
Unit pA

1	3.000
2	6.000
3	6.000
4	4.000
5	7.000
6	6.000
7	6.000
8	4.000
9	4.000
10	6.000
11	5.000

MEAN 5.182pA
SIGMA 1.250pA
MIN 3.000pA
MAX 7.000pA
QTY 11

TOTAL PASSED DEVICES : 11
TOTAL FAILED DEVICES : 0
NO REJECTED UNITS.

ELECTRICAL MEASUREMENTS

AFTER 50 KRad

DC AT 25 °C



MOTOROLA

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Centre Electronique de Toulouse*

MOTOROLA Semiconductors
HIGH RELIABILITY DIVISION
TRACEABILITY INFORMATION

PROCESS LOT NUMBER **NTTA0111H**
DEVICE **TY38356H**
SOURCE TYPE **LM111H**
DATE CODE **9504**
CUSTOMER **VARIOUS**
CUSTOMER PART NUMBER **SCC 9103 002 07B**
LOT SIZE **11**
SERIAL NUMBER RANGE **1-11**
MEASUREMENT TYPE **25 C RADIATION TESTING**
DATE **03-MAR-95**

COMMENTS

TABLE 2A DC PARAMETERS
ELECTRICAL RECORDS AFTER 50 Krad

PARAMETERS TEST CONDITIONS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
VCC	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	15.000 V	29.500 V	29.500 V	29.500 V	2.500 V
VEE	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-15.000 V	-500.000 mV	-500.000 mV	-500.000 mV	-2.500 V
VIC	0.000 V						-14.500 V	-14.500 V	-14.500 V	0.000 V
V6					15.000 V	15.000 V				
V5						15.000 V				

LIMITS

MIN	-2.000 mV	-10.000 nA	0.000 A	0.000 A	-2.000 mV	-10.000 nA	-10.000 nA	0.000 A	0.000 A	-2.000 mV
MAX	2.000 mV	10.000 nA	100.000 nA	100.000 nA	2.000 mV	10.000 nA	10.000 nA	100.000 nA	100.000 nA	2.000 mV

DATA RECORDS

Test Nb	1.0	3.0	4.0	5.0	6.0	8.0	13.0	14.0	15.0	16.0
Test	VIO1	IIO1	IIB1+	IIB1-	VIO3	IIO3	IIO2	IIB2+	IIB2-	VIO2
Unit	mV	nA	nA	nA	mV	nA	nA	nA	nA	mV
1 F	-1.554	14.326 *	66.809	52.483	-1.197	21.693 *	18.109 *	78.004	59.895	-2.093 *
2 F	-1.377	18.212 *	67.230	49.019	-1.017	18.095 *	21.695 *	74.514	52.819	-1.915
3 F	-0.838	14.507 *	49.046	34.540	-0.472	7.201	10.786 *	70.807	60.021	-1.376
4 F	-1.378	18.479 *	67.044	48.565	-0.839	14.502 *	21.717 *	77.952	56.235	-1.916
5 F	-0.837	14.494 *	56.398	41.904	-0.651	10.783 *	14.510 *	63.595	49.084	-1.377
6 F	-0.650	10.781 *	52.798	42.017	-0.291	3.589	7.196	63.612	56.417	-1.197
7 F	-1.196	14.506 *	67.204	52.698	-0.838	14.492 *	21.715 *	78.063	56.348	-1.735
8 F	-1.376	14.505 *	59.834	45.328	-0.837	14.499 *	21.691 *	78.096	56.406	-1.914
9 F	-1.196	21.739 *	56.154	34.415	-0.651	10.798 *	14.502 *	70.747	56.244	-1.735
10 F	-0.838	14.510 *	56.302	41.792	-0.292	3.585	10.774 *	74.552	63.778	-1.378
11	-0.291	0.366	30.819	30.454	-0.290	3.323	0.010	45.604	45.594	-0.837
MEAN	-1.048mV	14.220nA	57.240nA	43.020nA	-670.455uV	11.142nA	14.791nA	70.504nA	55.713nA	-1.588mV
SIGMA	385.842uV	5.429nA	10.868nA	7.503nA	308.814uV	6.201nA	7.146nA	9.871nA	5.077nA	283.338uV
MIN	-1.554mV	366.000pA	30.819nA	30.454nA	-1.197mV	3.323nA	10.000pA	45.604nA	45.594nA	-2.093mV
MAX	-291.000uV	21.739nA	67.230nA	52.698nA	-290.000uV	21.693nA	21.717nA	78.096nA	63.778nA	-837.000uV
QTY	11	11	11	11	11	11	11	11	11	11

TOTAL PASSED DEVICES : 1

TOTAL FAILED DEVICES : 10

REJECTED UNITS:

1,2,3,4,5,6,7,8,9,10

PARAMETERS TEST CONDITIONS

Test Nb 38.0
Test II
VCC 18.000 V
VEE -18.000 V

LIMITS

MIN 0.000 A
MAX 20.000 nA

DATA RECORDS

Test Nb 38.0
Test II
Unit pA

1	7.000
2	7.000
3	5.000
4	5.000
5	8.000
6	5.000
7	4.000
8	4.000
9	3.000
10	6.000
11	5.000

MEAN 5.364pA
SIGMA 1.502pA
MIN 3.000pA
MAX 8.000pA
QTY 11

TOTAL PASSED DEVICES : 11
TOTAL FAILED DEVICES : 0
NO REJECTED UNITS.

ELECTRICAL MEASUREMENTS

AFTER 168 H ANNEALING

DC AT 25 °C



MOTOROLA

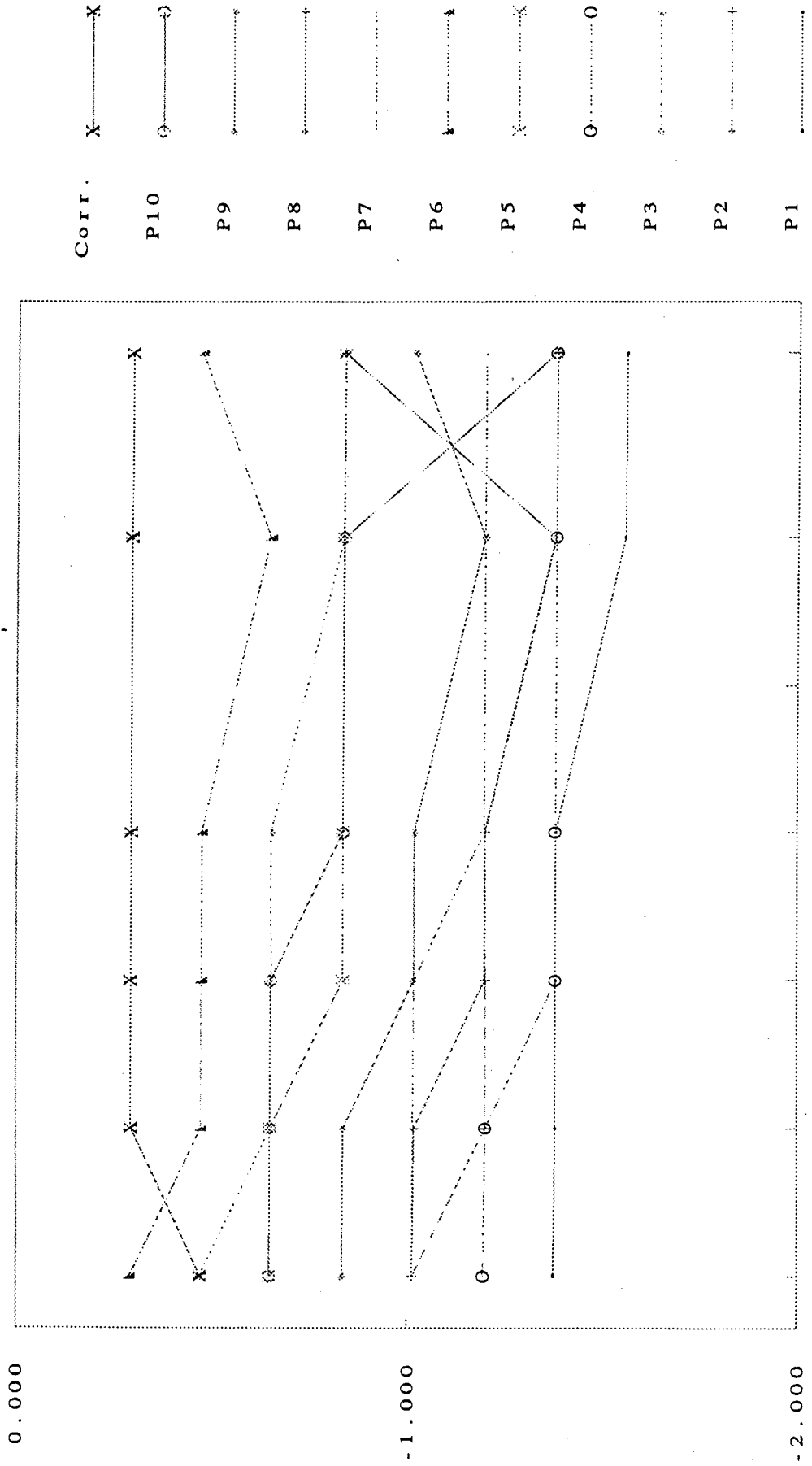
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TOTAL DOSE RADIATION TESTING
MOTOROLA FRANCE

Source: LM111H Lot: NTTA0111H Date Code: 9504 Date: 03-MAR-95

Test Nb=1.0 Test =VIO1 VCC =15.000 V

VEE =-15.000 V VIC =0.000 V



0K 10K 20K 30K 40K 50K 168H

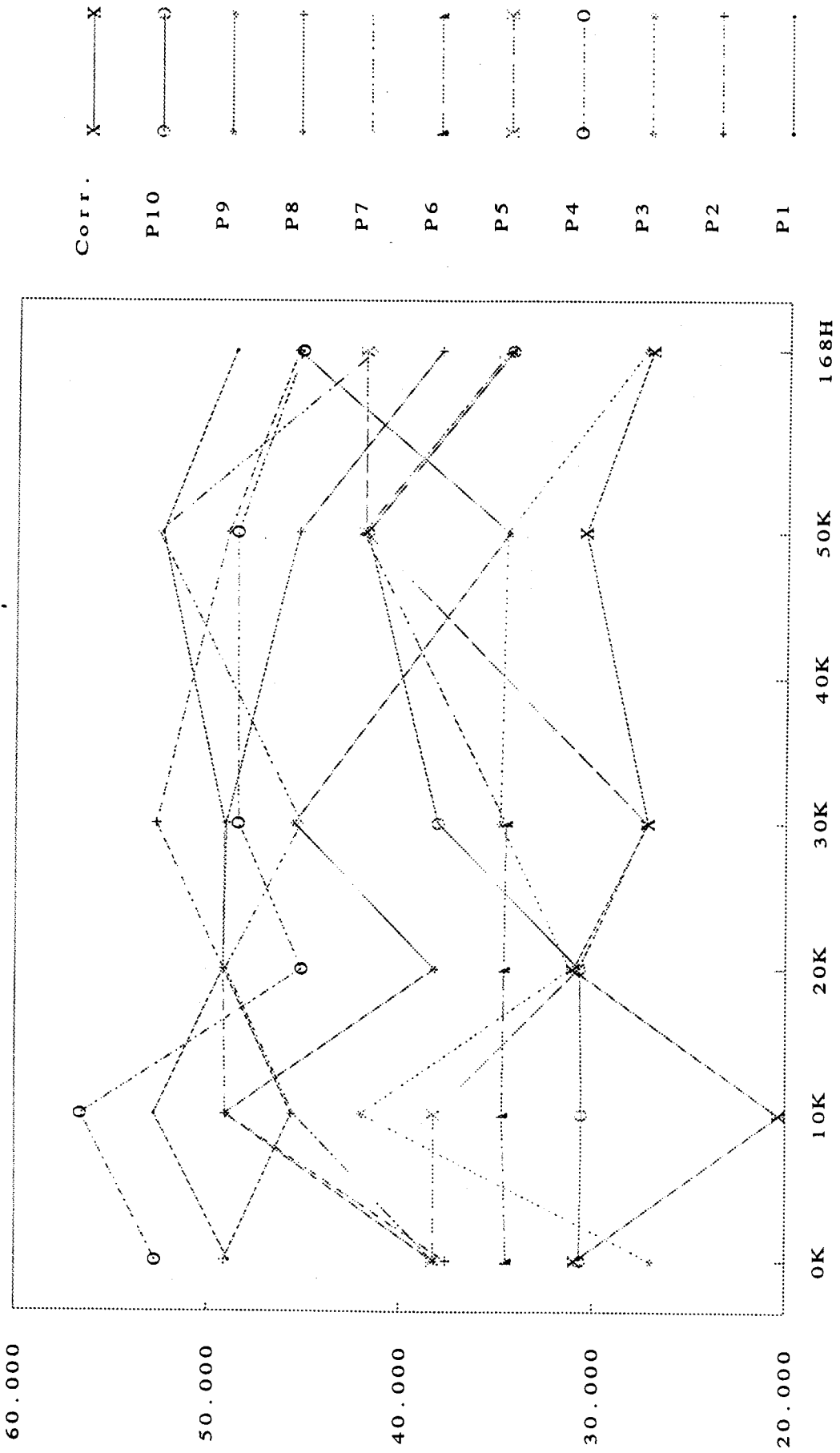
Limit min: -2.000 mV Limit max: 2.000 mV

Test 1.0 VIO1 (mV)

TOTAL DOSE RADIATION TESTING
MOTOROLA FRANCE

Source: LM111H Lot: NTTA0111H Date Code: 9504 Date: 03-MAR-95

Test Nb=5.0 Test = IIB1- VCC = 15.000 V
VEE = -15.000 V



Limit min: 0.000 nA Limit max: 100.000 nA

Devices Measurements

Test4.0 IIB1+(nA)

	0K	10K	20K	30K	50K	168H
Correl.	30.875	23.936	31.101	30.754	30.819	27.237
P1	48.902	56.410	56.418	60.040	66.809	63.263
P2	37.715	52.678	56.419	63.631	67.230	63.625
P3	27.005	45.615	41.941	45.582	49.046	41.914
P4	52.736	56.633	56.273	59.243	67.044	63.574
P5	38.249	41.828	41.793	41.872	56.398	56.410
P6	34.626	41.885	41.795	41.687	52.798	41.682
P7	38.267	49.081	56.424	56.038	67.204	59.781
P8	49.127	49.197	56.402	59.993	59.834	52.503
P9	38.253	49.108	45.565	56.398	56.154	60.033
P10	34.414	37.939	37.881	52.803	56.302	56.195
MEAN	39.929nA	48.037nA	49.091nA	53.729nA	59.882nA	55.898nA
SIGMA	7.944nA	6.266nA	7.901nA	7.978nA	6.777nA	8.264nA
MIN	27.005nA	37.939nA	37.881nA	41.687nA	49.046nA	41.682nA
MAX	52.736nA	56.633nA	56.424nA	63.631nA	67.230nA	63.625nA
CP	2.09795	2.6599	2.10931	2.08914	2.45933	2.0169
CPK	1.6754	2.55549	2.07097	1.93334	1.97327	1.77899